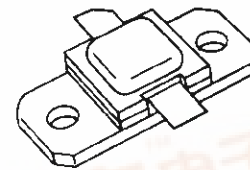




# AM1011-075

## RF & MICROWAVE TRANSISTORS L-BAND AVIONICS APPLICATIONS

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- 10:1 VSWR CAPABILITY
- LOW THERMAL RESISTANCE
- INPUT/OUTPUT MATCHING
- OVERLAY GEOMETRY
- METAL/CERAMIC HERMETIC PACKAGE
- $P_{OUT} = 75 \text{ W MIN. WITH } 9.2 \text{ dB GAIN}$



**.400 x .400 2LFL (S036)**  
hermetically sealed

**ORDER CODE**  
AM1011-075

**BRANDING**  
1011-75

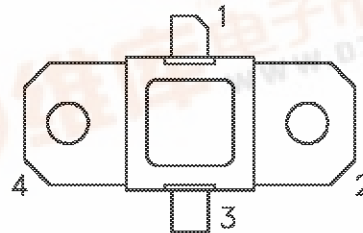
### DESCRIPTION

The AM1011-075 device is a high power Class C transistor specifically designed for L-Band Avionics transponder/interrogator pulsed output and driver applications.

This device is capable of operation over a wide range of pulse widths, duty cycles, and temperatures and is capable of withstanding 10:1 output VSWR at rated RF conditions. Low RF thermal resistance and computerized automatic wire bonding techniques ensure high reliability and product consistency.

The AM1011-075 is supplied in the AMPAC™ Hermetic Metal/Ceramic package with internal Input/Output matching structures.

### PIN CONNECTION



- |              |            |
|--------------|------------|
| 1. Collector | 3. Emitter |
| 2. Base      | 4. Base    |

### ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}\text{C}$ )

Symbol	Parameter	Value	Unit
$P_{DISS}$	Power Dissipation* ( $T_c \leq 100^{\circ}\text{C}$ )	175	W
$I_c$	Device Current*	5.4	A
$V_{CC}$	Collector-Supply Voltage*	55	V
$T_J$	Junction Temperature (Pulsed RF Operation)	250	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	- 65 to +200	$^{\circ}\text{C}$

### THERMAL DATA

$R_{\theta JA(j-c)}$	Junction-Case Thermal Resistance*	0.86	$^{\circ}\text{C/W}$
----------------------	-----------------------------------	------	----------------------

\*Applies only to rated RF amplifier operation

AM1011-075

ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)

STATIC

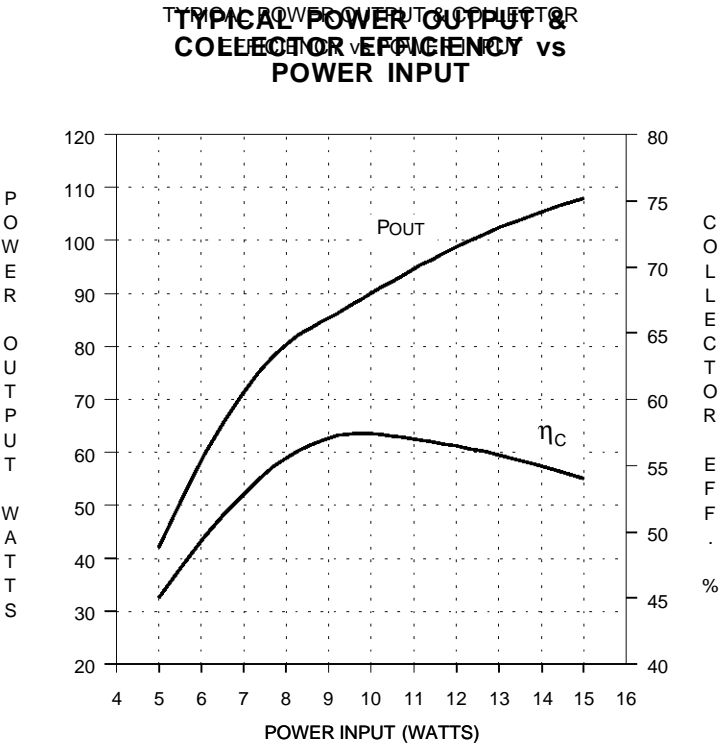
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV <sub>CBO</sub>	I <sub>C</sub> = 10mA	I <sub>E</sub> = 0mA	65	—	—	V
BV <sub>EBO</sub>	I <sub>E</sub> = 4mA	I <sub>C</sub> = 0mA	3.5	—	—	V
BV <sub>CER</sub>	I <sub>C</sub> = 20mA	R <sub>BE</sub> = 10Ω	65	—	—	V
I <sub>CES</sub>	V <sub>CE</sub> = 50V		—	—	6	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5V	I <sub>C</sub> = 1mA	10	—	—	—

DYNAMIC

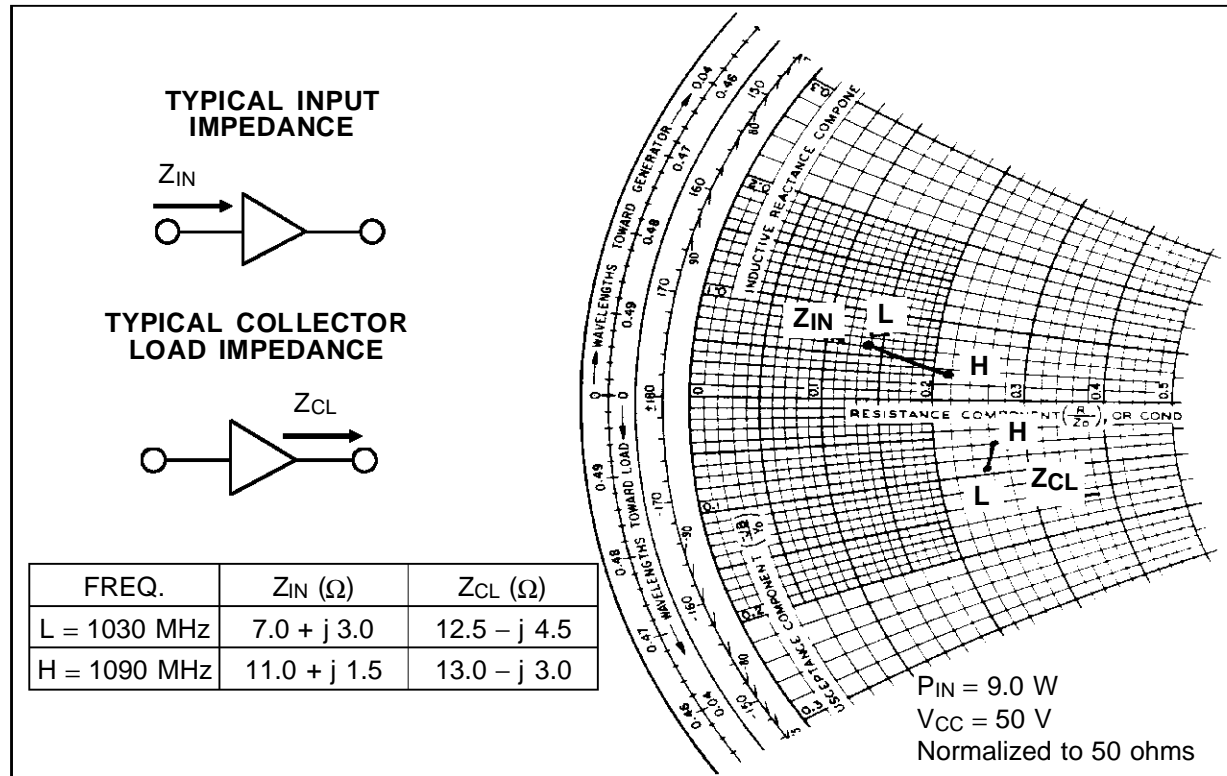
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P <sub>OUT</sub>	f = 1090MHz	P <sub>IN</sub> = 9W Peak	V <sub>CC</sub> = 50V	75	84	—	W
η <sub>c</sub>	f = 1090MHz	P <sub>IN</sub> = 9W Peak	V <sub>CC</sub> = 50V	48	56	—	%
G <sub>P</sub>	f = 1090MHz	P <sub>IN</sub> = 9W Peak	V <sub>CC</sub> = 50V	9.2	9.7	—	dB

Note: Pulse Width = 32μSec  
Duty Cycle = 2%

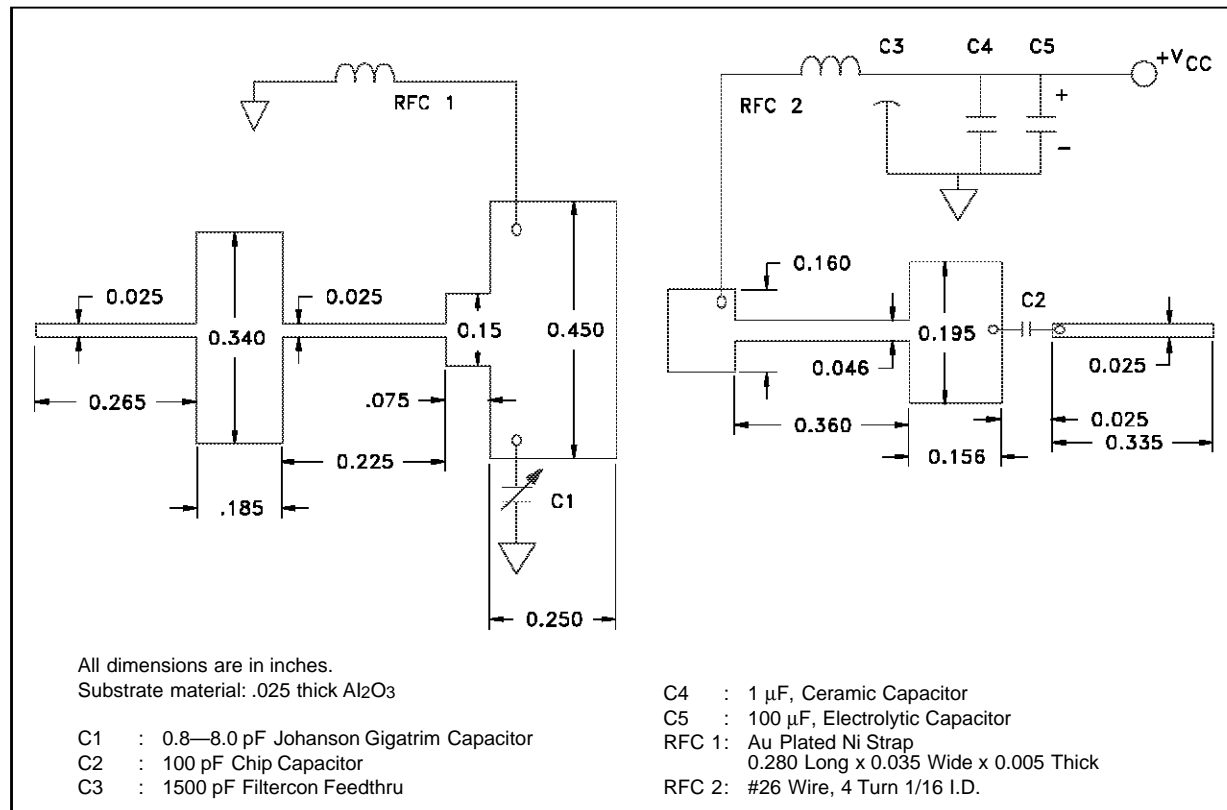
TYPICAL PERFORMANCE



## IMPEDANCE DATA

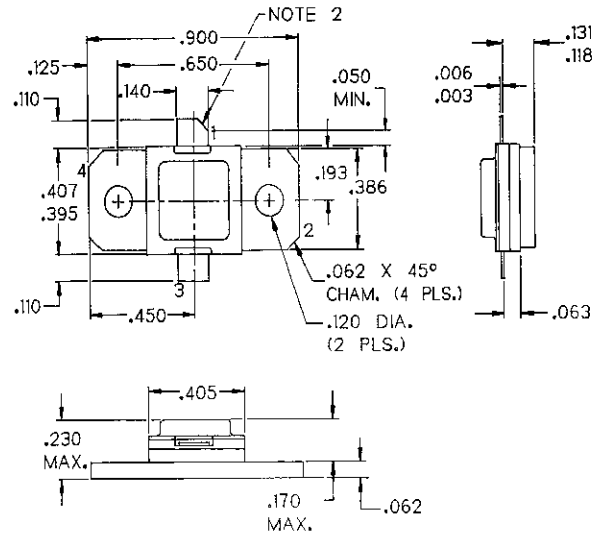


## TEST CIRCUIT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.: J133102E



NOTES:

1. ALL TOLERANCE  $\pm .010$  EXCEPT WHERE NOTED;  
DIMENSIONS IN INCHES.
2. COLLECTOR LEAD CHAMFER  $45^\circ$  NOM. X  $.040$  NOM.

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES  
Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -  
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A